

ABSTRACT OF THE DISCLOSURE

A fabrication method of VCSEL is used to form a contact electrode on a VCSEL in a resonance cavity. A heavily doped layer is formed in a resonance cavity where the light intensity is the weakest. A Bragg reflector is etched while the etching stop point being
5 above the heavily doped layer. Dopants are doped to form a high-carrier-concentration ohmic channel as a connection between an electrode and the heavily doped layer. Thereby, a contact electrode is formed on the VCSEL structure in the resonance cavity without the need of high etching precision.